Electronic Supplementary Material (ESI) for Journal of Materials Chemistry A.

Supplementary information

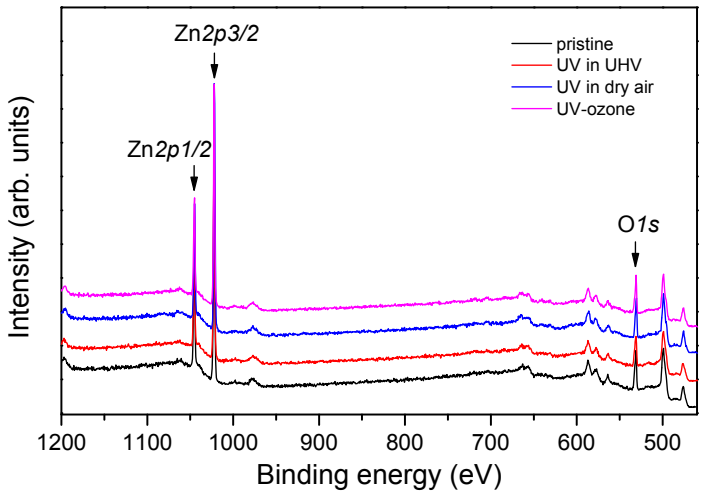

Fig. S1 XPS survey spectra of ZnONP film before and after UV-light soaking in UHV, dry air and UV-ozone.

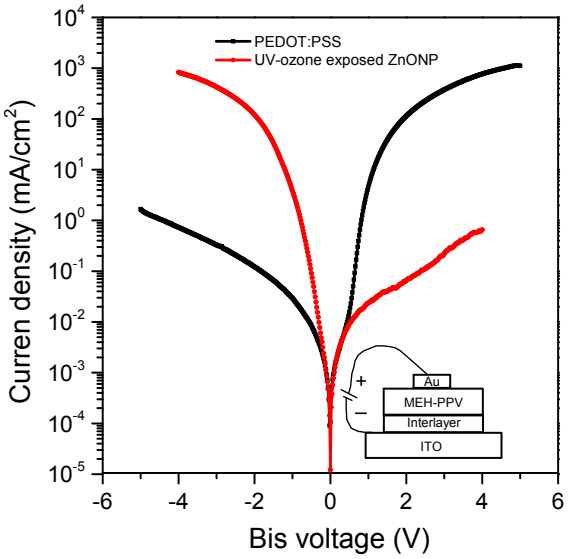

Fig. S2 J-V characteristics of the diode with structure of ITO/PEDOT:PSS or UV-ozone exposed ZnONP/MEH-PPV/Au .

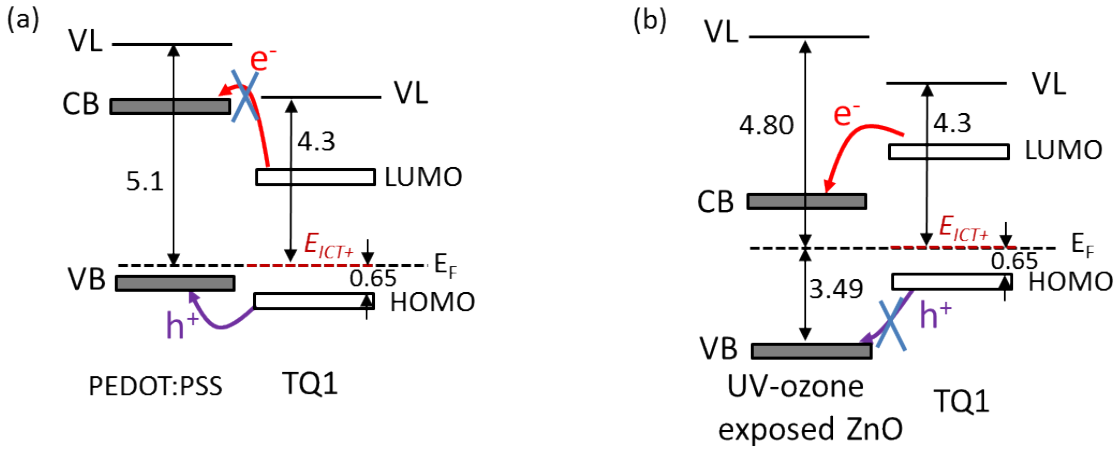

Fig. S3 Energy level alignment diagrams at (a) TQ1/PEDOT:PSS interface and (b) TQ1/UV-ozone exposed ZnONP interface.

Table S1: Work function (WF) and Ionization Potential (IP) measured by UPS for a series of ZnONP films spun-coated from solution, each row corresponding to a different ZnONP formulation, illustrating the range of WF and IP that can be obtained. The WF and IP values are obtained with an accuracy of ± 0.05 eV.

Supplier	WF (eV)	IP (eV)
Genes'Ink	3.88	7.84
Genes'Ink	4.00	7.83
Genes'Ink	3.97	7.88
Genes'Ink	3.90	7.89
Genes'Ink	3.96	7.92
Genes'Ink	3.60	7.94
Genes'Ink	3.65	7.77
Genes'Ink	3.81	7.74
Genes'Ink	3.67	7.63
Genes'Ink	3.93	7.95
Genes'Ink	3.79	7.82
Genes'Ink	3.75	7.83
CNRS	3.92	8.00
CNRS	3.98	8.03
CNRS	3.98	8.02
CNRS	3.89	7.98
CNRS	3.88	7.96
CNRS	4.02	7.66
CNRS	4.00	7.91